BUK7K35-60E

Dual N-channel 60 V, 30 m Ω standard level MOSFET

15 November 2013

Product data sheet

1. General description

Dual standard level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	20.7	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	38	W
Static characte	Static characteristics FET1 and FET2						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 11$		-	24	30	mΩ
Dynamic characteristics FET1 and FET2							
Q_{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 14}}; \underline{\text{Fig. 13}}$		-	4.7	-	nC



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Pinning information

Table 2. **Pinning information**

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	O O O	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	2	

Ordering information

Table 3. **Ordering information**

Type number	Package				
	Name	Description	Version		
BUK7K35-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205		

Marking

Table 4. Marking codes

Type number	Marking code
BUK7K35-60E	73560E

Limiting values 8.

Table 5. **Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω	-	60	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC	-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	20.7	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>	-	17	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 4	-	95	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>	-	38	W
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Symbol	Parameter	Conditions		Min	Max	Unit
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C
Source-drain diode FET1 and FET2						,
Is	source current	T _{mb} = 25 °C		-	20.7	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	95	Α
Avalanche Ruggedness FET1 and FET2						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 20.7 A; $V_{sup} \le 60 \text{ V}$; V_{GS} = 10 V; $T_{j(init)}$ = 25 °C; Fig. 3	[1][2]	-	20.3	mJ

- 1] Refer to application note AN10273 for further information
- [2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C

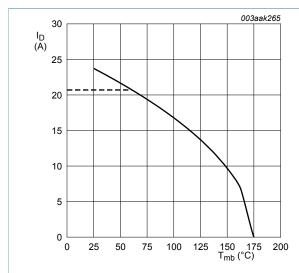


Fig. 1. Continuous drain current as a function of mounting base temperature

 $V_{GS} \ge 10V$

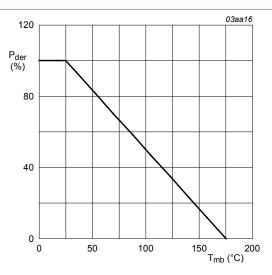


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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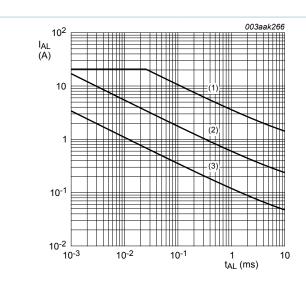
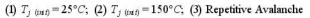


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time



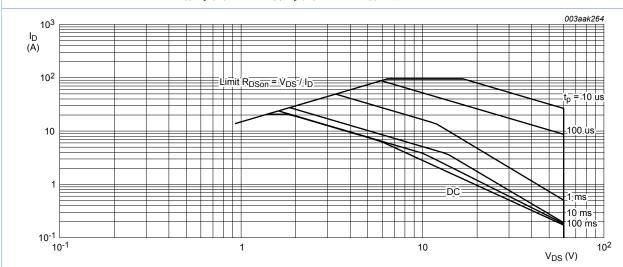


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

 $T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

9. Thermal characteristics

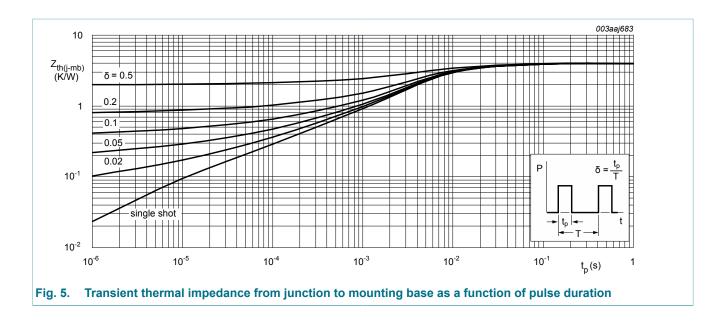
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	3.96	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit	
Static chara	acteristics FET1 and FET2		-				
(BIT)DOO	drain-source	I _D = 250 μA; V _{GS} = 0 V; T _j = -55 °C	54	-	-	V	
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V	
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V	
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9; Fig. 10	1	-	-	V	
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9; Fig. 10	-	-	4.5	V	
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μΑ	
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA	
I _{GSS} gate leakage c	I _{GSS}	gate leakage current	V_{GS} = -20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA	
R _{DSon}	drain-source on-state	V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 11</u>	-	24	30	mΩ	
	resistance	V _{GS} = 10 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 11	-	54	67	mΩ	
Dynamic ch	aracteristics FET1 and FE	T2	1				
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 10 V; T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	12.5	-	nC	
Q_{GS}	gate-source charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 10 V;	-	2.8	-	nC	
Q_{GD}	gate-drain charge T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 13</u>	-	4.7	-	nC		

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Parameter	Conditions		Min	Тур	Max	Unit
gate-source plateau voltage	I _D = 5 A; V _{DS} = 48 V; T _j = 25 °C; Fig. 14; Fig. 13		-	4.9	-	V
input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	596	794	pF
output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	97	117	pF
reverse transfer capacitance	-		-	67	92	pF
turn-on delay time	V_{DS} = 48 V; R_{L} = 10 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω ; T_{j} = 25 °C; I_{D} = 5 A		-	5.2	-	ns
rise time			-	7	-	ns
turn-off delay time			-	10	-	ns
fall time			-	7.2	-	ns
diode FET1 and FET2	1	I				
source-drain voltage	$I_S = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}; Fig. 16$		-	0.8	1.2	V
reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	18.5	-	ns
recovered charge	$V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$		-	15.2	-	nC
	gate-source plateau voltage input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time diode FET1 and FET2 source-drain voltage reverse recovery time	gate-source plateau voltage $I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; T_j = 25 ^{\circ}\text{C};$ Fig. 14; Fig. 13 input capacitance output capacitance $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 ^{\circ}\text{C}; \text{ Fig. 15}$ reverse transfer capacitance turn-on delay time $V_{DS} = 48 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5 \Omega; T_j = 25 ^{\circ}\text{C}; I_D = 5 \text{ A}$ turn-off delay time fall time $I_{S} = 5 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; \text{ Fig. 16}$ reverse recovery time $I_{S} = 5 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{S} = 30 \text{ V}; T_{S} = 25 ^{\circ}\text{C}$	gate-source plateau voltage $I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; T_j = 25 \text{ °C};$ Fig. 14; Fig. 13 input capacitance $V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $V_{JS} = 25 \text{ °C}; Fig. 15$ reverse transfer capacitance $V_{DS} = 48 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$ rise time $V_{DS} = 48 \text{ V}; R_L = 10 \Omega; V_{GS} = 10 \text{ V};$ $V_{JS} = 10 \text{ V}; R_{JS} = 10 \text{ V};$ $V_{JS} = 10 \text{ V}; R_{JS} = 10 \text{ V};$ $V_{JS} = 10 \text{ V}$	gate-source plateau voltage $I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; T_j = 25 \text{ °C};$ - reverse transfer capacitance $I_D = 5 \text{ A}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - reverse transfer capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 15$ - coutput capacitance $I_J = 25 \text{ °C}; Fig. 16$ - coutput capacitance $I_J = 25 \text{ °C}; I_J = 25 °$	gate-source plateau voltage $I_D = 5 \text{ A}$; $V_{DS} = 48 \text{ V}$; $T_j = 25 \text{ °C}$; - 4.9 input capacitance $V_{GS} = 0 \text{ V}$; $V_{DS} = 25 \text{ V}$; $f = 1 \text{ MHz}$; - 596 output capacitance $T_j = 25 \text{ °C}$; Fig. 15 - 97 reverse transfer capacitance - 67 turn-on delay time $V_{DS} = 48 \text{ V}$; $R_L = 10 \Omega$; $V_{GS} = 10 \text{ V}$; - 5.2 rise time $R_{G(ext)} = 5 \Omega$; $T_j = 25 \text{ °C}$; $I_D = 5 \text{ A}$ - 7 turn-off delay time - 10 fall time - 7.2 diode FET1 and FET2 - 0.8 reverse recovery time $I_S = 5 \text{ A}$; $V_{GS} = 0 \text{ V}$; $T_j = 25 \text{ °C}$; Fig. 16 - 0.8 reverse recovery time $I_S = 5 \text{ A}$; $I_S = 5 \text{ C}$; $I_S = 5 \text{ C}$ - - 18.5	gate-source plateau voltage $I_D = 5 \text{ A}$; $V_{DS} = 48 \text{ V}$; $T_j = 25 ^{\circ}\text{C}$; - 4.9 - input capacitance $V_{GS} = 0 \text{ V}$; $V_{DS} = 25 \text{ V}$; $f = 1 \text{ MHz}$; - 596 794 output capacitance $T_j = 25 ^{\circ}\text{C}$; Fig. 15 - 97 117 reverse transfer capacitance - 67 92 turn-on delay time $V_{DS} = 48 \text{ V}$; $R_L = 10 \Omega$; $V_{GS} = 10 \text{ V}$; - 5.2 - rise time $R_{G(ext)} = 5 \Omega$; $R_{G(ext)} = 5 $

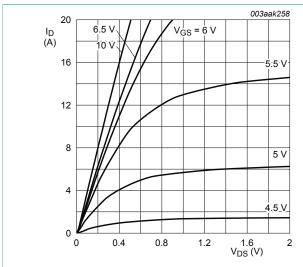


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

 $T_j = 25$ °C

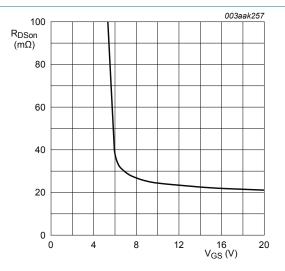


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25^{\circ}C; \ I_D = 5A$$

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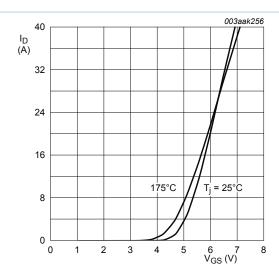


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

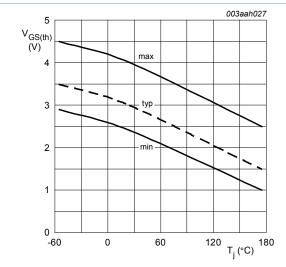


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

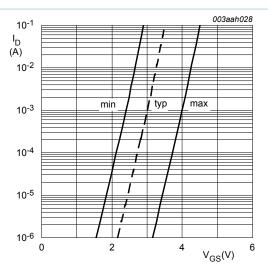


Fig. 9. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

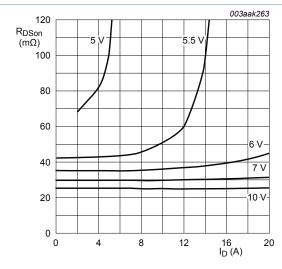


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25^{\circ}C$$

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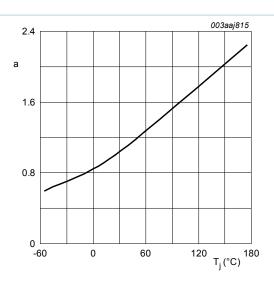


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

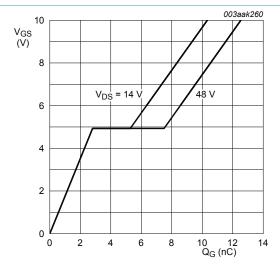


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25$$
°C; $I_D = 5A$

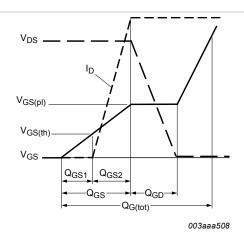


Fig. 13. Gate charge waveform definitions

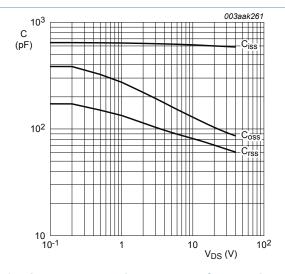


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = \mathbf{0}V; f = \mathbf{1}MHz$$

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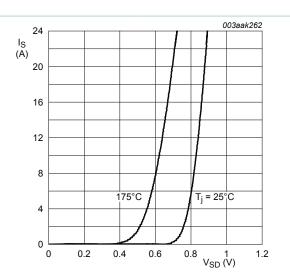
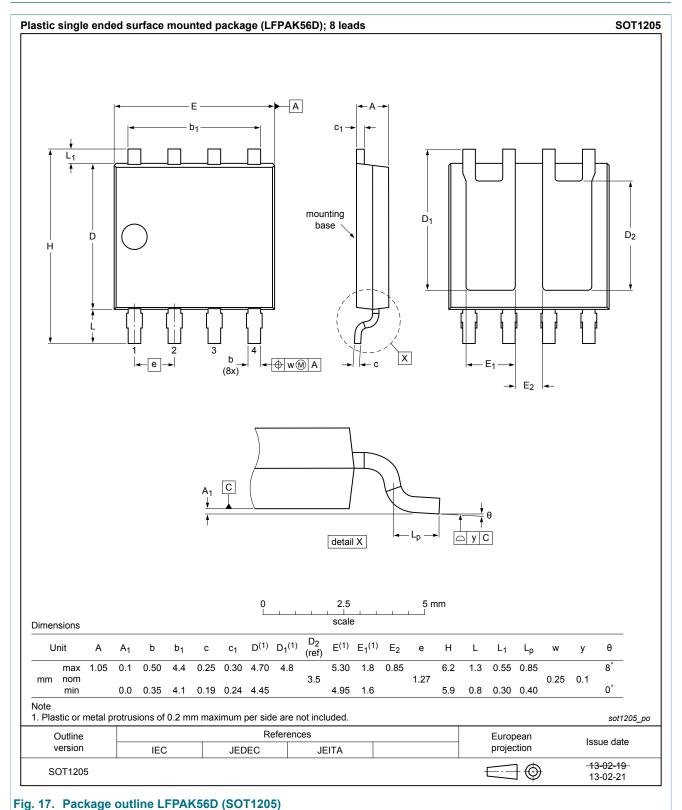


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$$V_{GS} = 0V$$

11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
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